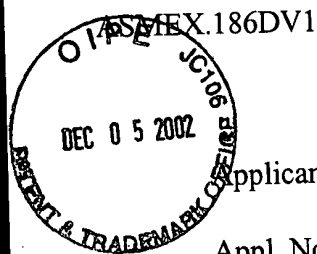


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PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Raaijmakers et al.

Appl. No. : 09/764,711

Filed : January 18, 2001

For : METHOD OF DEPOSITING
SILICON WITH HIGH STEP
COVERAGE

Examiner : Angel Roman

) Group Art Unit 2812

) I hereby certify that this correspondence and all
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) Arlington, VA 22202, on

) December 2, 2002

) (Date)

) Adeel S. Akhtar
) Adeel S. Akhtar, Reg. No. 41,394

AMENDMENT ACCOMPANYING REQUEST
FOR CONTINUED EXAMINATION

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

In response to the Office Action mailed on August 1, 2002, Applicants respectfully request full consideration of the remarks contained herein.

REMARKS

In the Office Action mailed on August 1, 2002, the Examiner rejected all pending claims. Applicants respectfully request reconsideration of the rejections in view of the remarks contained herein.

Obviousness Rejections

The Examiner has rejected Claims 33-37 as being unpatentable over Vo (U.S. Patent No. 5,097,381A) in view of Mazuré et al. (U.S. Patent No. 5,677,219). The Examiner stated that "Vo lacks anticipation on disclosing an specific method used to form the heavily doped polysilicon." To satisfy this deficiency, the Examiner stated that "Mazuré et al. discloses an as deposited doping process for forming a polysilicon plug doped with arsenic for a trench capacitor." Thus, the Examiner stated that "it would have been obvious to a person having ordinary skills in the art

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